

Application/Control Number: 10/537,158
Art Unit: 1762
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Specification Amendments

Please amend the specification to add the following paragraph on page 5, after line 27 and before "DESCRIPTION OF PREFERRED EMBODIMENTS".

-- BRIEF DESCRIPTION OF THE DRAWINGS

Figure 1 shows examples of rotaxanes used to demonstrate the process.

Figure 2 shows a schematic illustration of the dynamical process of the present invention

Figure 3 shows examples of dot writing on the surface of thin films of rotaxane 1 in Figure 1, on graphite substrate.

Figure 3a shows an array of nanostructures.

Figure 3b shows parallel lines of different fabricated length that yielded different number of dots.

Figure 3c shows the application of the process on a 30x30 square micrometer, with 31 lines consisting of 45 dots each.

Figure 3d shows an application of the process for dot writing to the storage of hexadecimal numbers in the form of parallel strings.

Figure 4 shows the linear relationship between the number of dots and the scan length for a film of preset thickness.

Figure 5 shows the value of inter-dot spacing (left axis), the dot diameter and height (right axis) versus film thickness.

Figure 6 shows a schematic illustration of the static process of the present invention.

Figure 7 shows an ATM image result of the morphological re-organization following the static process. --